

**ABSTRACT**

A method and system for providing at least one contact in a flash memory device is disclosed. The flash memory device includes a plurality of gate stacks and at least one component including a polysilicon layer as a top surface. The method and system further include forming a silicide on the top surface of the polysilicon layer and providing an insulating layer covering the plurality of gate stacks, the at least one component and the silicide. The method and system also include etching the insulating layer to provide at least one contact hole. The insulating layer etching step uses the silicide as an etch stop layer to ensure that the insulating etching step does not etch through the polysilicon layer. The method and system also include filling the at least one contact hole with a conductor.

2025 RELEASE UNDER E.O. 14176